PNP/NPN Epitaxial Planar Silicon Transistors



## 2SA1683/2SC4414

# Low-Frequency General-Purpose Amplifier, Low-Frequency Power Amplifier Applications

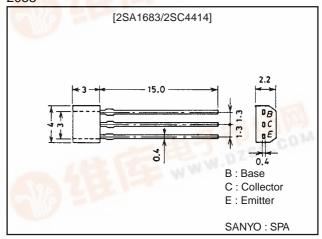
#### **Features**

- · Adoption of FBET process.
- $\cdot$  High breakdown voltage :  $V_{\mbox{\scriptsize CEO}}\!\!>\!\!80\mbox{\scriptsize V}.$

## **Package Dimensions**

unit:mm

2033



(): 2SA1683

## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)100	V	
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(–)80	V	
Emitter-to-Base Voltage	V <sub>EBO</sub>	110	(–)5	V	
Collector Current	Ic		(-)500	mA	
Collector Current (Pulse)	ICP	THE VIEW WILL	(–)800	mA	
Base Current	IB		(-)100	mA	
Collector Dissipation	PC	00//0 -	300	mW	
Junction Temperature	Tj		150	°C	
Storage Temperature	Tstg	440	-55 to +150	°C	

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Unit		
Falametel	Symbol	Conditions		typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)60V, I <sub>E</sub> =0			(-)0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(-)0.1	μA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)50mA	100*		400*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)400mA	60	M . D .		
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)10mA	W	120		MHz

 $\ast$  : 2SA1683/2SC4414 are classified by 50mA  $h_{FE}$  as follows :

I	100	R	200	140	S	280	200	Т	400	
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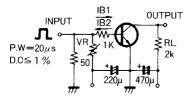
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## SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters

### 2SA1683/2SC4414

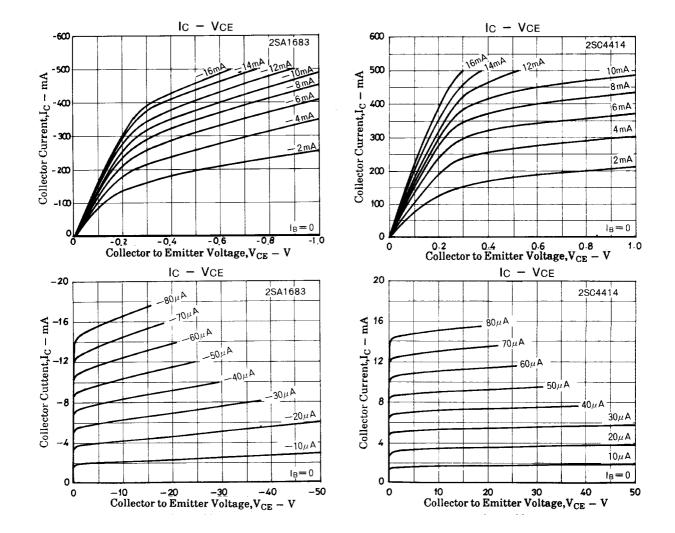
Parameter	Symbol	Conditions	Ratings			Unit
Falametei	Symbol	Conditions		typ	max	Utill
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)400mA, I <sub>B</sub> =(-)40mA		0.16	(-)0.5	V
				(-0.20)		V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)400mA, I <sub>B</sub> =(-)40mA		(–)0.9	(-)1.2	V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		(7)5		pF
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	$I_{C}=(-)10\mu A, I_{E}=0$	(–)100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(–)1mA, R <sub>BE</sub> =∞	(–)80			V
Emitter-to-Base Breakdown Votage	V(BR)EBO	$I_{E}=(-)10\mu A, I_{C}=0$	(–)5			V
Turn-ON Time	<sup>t</sup> ON	See specified Test Circuit		50		ns
Storage Time		See specified Test Circuit		(500)		ns
Storage Time	t <sub>stg</sub>			650		
Fall Time	t <sub>f</sub>	See specified Test Circuit		(80)90		ns

#### **Switching Time Test Circuit**

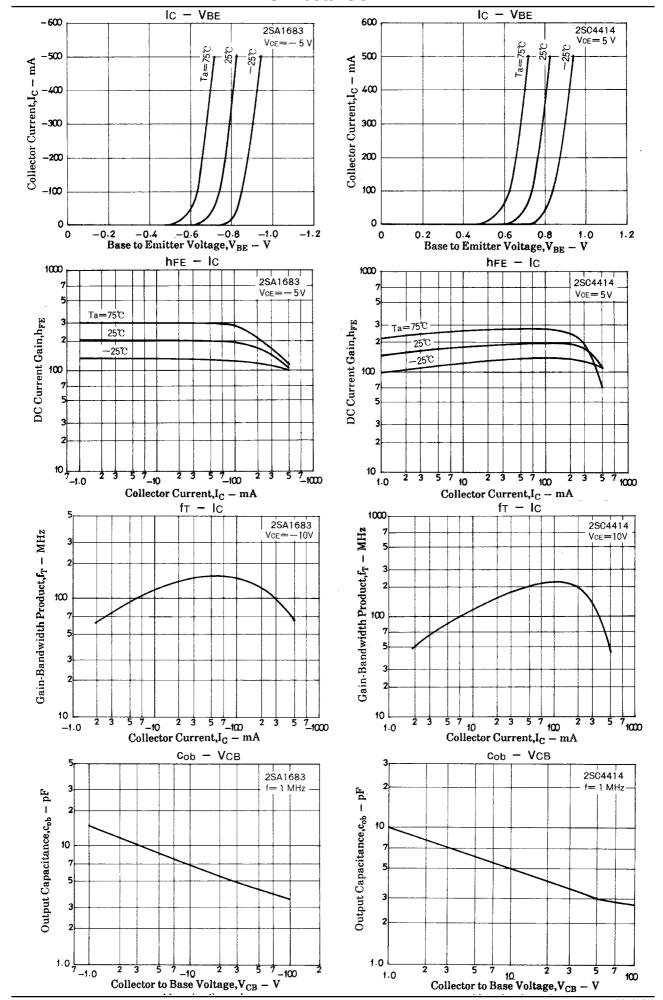


 $V_{BE}$ =-5V,  $V_{CC}$ =20V 10I<sub>B1</sub>=-10I<sub>B2</sub>=I<sub>C</sub>=200mA (For PNP, the polarity is reserved.)

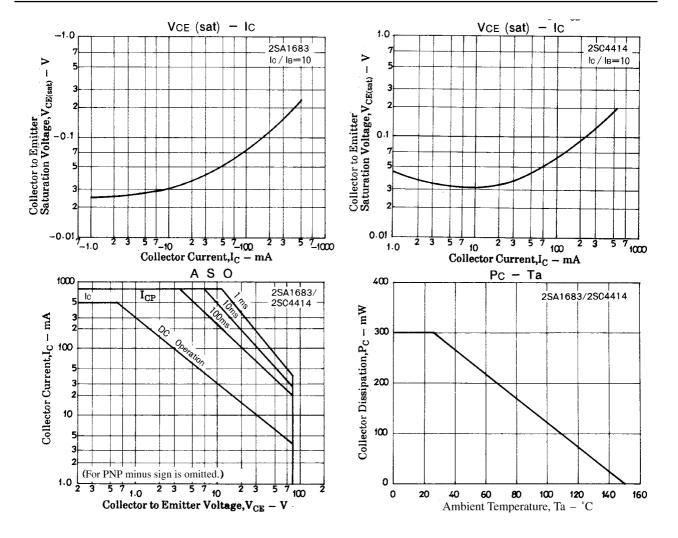
Unit (resistance :  $\Omega$ , capacitance : F)



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